C om puting C ounterion D ensities at Interm ediate C oupling

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By decomposing the C oulomb interaction into a long distance component appropriate for meaneld theory, and a nonmean-eld short distance component, we compute the counterion density near a charged surface for all values of the counterion coupling parameter. A modied strong-coupling expansion that is manifestly nite at all coupling strengths is used to treat the short distance component. We nd a nonperturbative correction related to the lateral counterion correlations that modies the density at intermediate coupling.

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The rise of biological physics has rekindled the longstanding interest in aqueous electrostatics [1]. Poisson-Boltzm ann m ean-eld theory fails to describe a number of striking phenom ena, such as charge inversion [2, 3] and counterion-mediated attraction [4, 5, 6, 7, 8, 9, 10], that occur when strong correlations develop between multivalent counterions. Although there has been som e success understanding counterion correlations using both a phenom enological W igner crystal theory [3], and system atic weak-coupling (WC) [11] and strong-coupling (SC) [12, 13, 14] expansions, a complete quantitative theory spanning the entire range of counterion behavior is still lacking. This letter introduces a method to com pute the counterion density at interm ediate coupling by decomposing the Coulomb interaction into long and short distance components in the spirit of the Weeks-Chandler-Andersen theory of simple uids [15]. This decom position not only gives good quantitative agreem ent with simulations, it also provides a natural fram ework to understand both the success of SC expansion, as well as the role that lateral correlations play in the counterion density.

Here, I use mean-eld theory for the long distance interaction, and introduce a modi ed SC expansion at short distances. The traditional SC expansion [12] is problem atic because it is form ally a virial expansion, and one naively expects it to be invalid precisely when the counterions are strongly interacting. Nonetheless, num erical simulations have demonstrated that it not only correctly predicts the average counterion density in the strong-coupling limit, but also computes the form of the corrections [14]. In contrast, the modi ed SC expansion introduced here is manifestly nite in the limit of in nite counterion coupling, but recovers the SC corrections at large, nite coupling.

In addition, this decomposition correctly reproduces the counterion distribution around a charged surface at both strong- and weak- coupling, and agrees very well with simulations at interm ediate coupling. A test-charge theory (TCT) which also computes approximate counterion densities at interm ediate coupling and explains the exponential form in the strong coupling lim it fails to elucidate the physics behind the corrections to that lim it in a clear and satisfactory manner [16]. Furthermore, I nd a nonperturbative correction to the density related to the lateral counterion correlations that becomes in portant at intermediate coupling. Unlike in SC theory, I can unambiguously compute an expression for the free energy and show that these lateral correlations play a role.

C onsider the primitive model for a charged surface neutralized by pointlike counterions of the opposite charge in a dielectric medium with dielectric constant, . To proceed, introduce a length scale, ', and de ne $V_s\left(r\right) = l_B Q^2 e^{re}$ '=r and $V_1\left(r\right) = l_B Q^2 (1 e^{re})=r$, where $l_B = e^2 = (~k_B T)$ is the B jerrum length and Q is the counterion valence. The length ' is currently arbitrary and will be chosen later to optimize the calculation. The Ham iltonian for ions of charge Q e centered at positions R interacting with a surface of charge density $n_f\left(r\right) = (z)$ is given by

$$H = \frac{1}{2} d^{3}rd^{3}r^{0} (r) [V_{s}(r r^{0}) + V_{1}(r r^{0})] (r^{0}); (1)$$

where $(r) = n_f(r) = Q$ (r R). It is understood in this expression that ion self-interactions, which arise only from $V_s(r)$, are to be neglected. The long range interaction can be decoupled by introducing a continuous eld through a Hubbard-Stratonovich transform ation, resulting in the action $S^0 = S_s + S_1$, where

$$S_{s} = \frac{1}{2} \int_{X}^{Z} d^{3}r d^{3}r^{0} \frac{n_{f}(r)}{Q} V_{s}(\dot{r} r^{0}) \frac{n_{f}(r)}{Q}$$

$$X Z d^{3}r n_{f}(r) V_{s}(\dot{r} R) = Q \qquad (2)$$

R 1);

$$= 4 \ \lim_{Z} Q^{2}, \text{ and}$$

$$= \frac{1}{2 \ _{B}} \ d^{3}r[(r \)^{2} + \ ^{2}(r^{2} \)^{2}] + i \ d^{3}r \ \underline{(r) \ (r)}$$
(3)

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The counterion positions, $R\,$, are restricted to be over the volum e of space that can be occupied by the counterions.

In the G rand C anonical ensemble for the counterions, the partition function is

$$Z / X = \frac{1}{N!} \frac{2}{N!} \frac{2}{N} D = d^{3}R e^{S^{0}};$$
 (4)

where the length 1 is de ned by $^2=`_B = e = a^3$, a is the counterion radius, and is the chemical potential [11]. Now de ne the partial partition function with integrals only over the counterion positions,

$$Z_{s} = \frac{X^{1}}{N} \frac{1}{N} \frac{1}{N} \frac{Z}{N} \frac{Y^{1}}{M} d^{3}R _{0} (R)$$

$$= \frac{X^{1}}{2} \frac{1}{N} \frac{X^{2}}{2} = 1 \qquad 3$$

$$= \frac{X^{2}}{N} \frac{X}{V_{s}} (R R)^{5} (5)$$

where $_0$ = (2 = $_B^{`}$)e^F $^+$ i , and F (r) = ${}^R d^3r^0 \; V_s \; (jr^0 \; r)n_f \; (r^0)$ =Q . This leaves Z / D e S , where

$$S = \frac{1}{{}_{B}}^{2} d^{3}r \frac{1}{2} (r)^{2} + \frac{\sqrt{2}}{2} r^{2} \ln Z_{s} [0 (r)]:$$
(6)

The average counterion density can be formally computed as h (r)i = $\ln Z_s = F(r)$.

Since this formulation is exact, the partition function is independent of the choice of `. To proceed, make the following approximations: (1) the mean-eld approximation for the long-distance interaction (saddle point in), and (2) expand the e ective potential $\ln Z_s[_0]$ using a modi ed SC-like cluster expansion described below. Making these approximations, the theory will lose its independence on the choice of ', and there will be a \best" `w hose value gives the closest agreem ent with the full theory. In principle, its value should be determ ined by optim izing the error between a loop expansion on the long-distance interaction and perturbative corrections to the short-distance expansion. On physical grounds, how ever, we argue that $\downarrow Q^2$, or, in other words, \downarrow is the distance that xed counterions interact with an energy of k_B T. Counterions at separations larger than this interact weakly, and mean-eld theory is likely valid above this length scale. In addition, the distinction between short and long length scales should not depend on the geometry of the xed charge distribution, and can therefore only depend on the B jerrum length and counterion valence. For concreteness, I will choose $' = \frac{1}{2}Q^2$.

The mean-eld approximation, given by S = 0, results in the equation

$$r^{2}$$
 $r^{4} + h (r)i = n_{f}(r) h = Q;$ (7)

where I have performed the W ick rotation ! i in the complex plane for convenience. The SC expansion can be

reproduced by expanding $\ln Z_{\rm s}$ in powers of $_{\rm 0}$ (z). How-ever, for counterions in the presence of a charged surface with charge density , each term of this expansion diverges as the coupling constant = 2 $l_{\rm B}$ Q³! 1 indicating that the counterion interactions are not small; this divergence can be absorbed by shifting 2 and utilizing overall charge neutrality [12].

Instead, expand in powers of $_{0}(z) = _{0}(z)$ 2=('_B) (z), where = (2 $\frac{1}{2}$ Q)¹ is the Gouy-Chapman length for a surface of charge density . This has the property that dz $_{0}(z) = 0$ due to overall charge neutrality, and yields

$$Z_{s} = \frac{X}{n} \frac{1}{n!} \frac{Z}{2} \frac{Y^{n}}{r^{n}} \frac{Y}{r^{2}} \frac{Y}{r^{n}} \frac{Y}{r^{2}} \frac{Y}{r^{n}} \frac{Y}{r^{2}} \frac{Y$$

where r indicates the position of a counterion projected to the surface, z its plistance from the surface, and γ_0 (r;z) = hexp[$_iV_s$ (r r_i ;z)] $i_{p=0}$ (r;z). Here, h $_p$ is the average taken with respect to the partition function

$$Z_{p} = \frac{X}{m} \frac{1}{m!} \frac{2}{B} \prod_{i=1}^{m} \frac{Z}{i} \sum_{j=1}^{m} \frac{Z}{m} \sum_{i< j}^{n} \frac{X}{m} \sum_{j=1}^{n} \frac{X}{m} \sum_{i< j}^{n} \frac{X}{m} \sum_{j=1}^{n} \frac{X}{m} \sum_{i< j}^{n} \frac{X}{m} \sum_{j=1}^{n} \frac{X}{m} \sum_{j=1}^$$

The expression hexp $\begin{bmatrix} i & V_s (r & r_i; z &) \end{bmatrix}_{i_p}^{i_p}$ represents the interaction of a charge at coordinates (r; z) with a layer of counterions at positions $(r_i; z_p = 0)$. In deriving Eq. (8), I have assumed h exp $\begin{bmatrix} i & V_s (r & r_i; z &) \end{bmatrix}_{i_p}^{i_p}$ hexp $\begin{bmatrix} i & V_s (r & r_i; z &) \end{bmatrix}_{i_p}^{i_p}$, which is true as long as the counterions at z > 0 are far enough apart compared to `.

and the interactions become predom inantly long-ranged. It is useful to de ne $\sim_0 = e^{(z)} (z)$ with exp[(r;z)]= hexp[F(z)] $_i V_s (r r; 0)$]i. The function (z) can be interpreted as the short-distance interaction potential of a charge at height z with the charged surface and with a layer of counterions at z = 0. Therefore, it encodes the response of the z = 0 layer to the presence of a charge at some z > 0, and is rem iniscent of theTCT [16]. One di erence between (z) and the TCT, how ever, is that

(z) also depends, at least in principle, on the shortrange structure of the counterions induced by the shortrange interaction. To develop a simple approximation for (z) which I will use throughout the remainder of the letter, assume that each counterion at z > 0 interacts with a uniform distribution of charge at z = 0 containing an induced circular correlation hole of radius $r_0 = \frac{r_B}{B} = 2 = \frac{r_B}{Q} =$. This approximates the size of a vacancy in a locally ordered lattice of counterions at the surface, which should be valid when is large. Thus, $(z) = (2) e^{zz} e^{\frac{r_B}{r_0^2 + z^2}}$. It is interesting that, for z, $(z) (1 e^{r_0 - 2}) z = is$ dominated by the interaction of the counterions with the bare surface and not the z = 0 layer of counterions whose contribution is of order $z^2 = (2) z = .$

To lowest order, h i= γ_0 , and the mean-eld equation for a charged surface now reads

where is the surface charge density. For small z, (z) F (z) is analytic and can be expanded as a power series in $(z=')^2$. On the other hand, F (z) is nonanalytic at z = 0 and contributes to the boundary conditions. This additional contribution can be disentangled by de ning F. In term sof, (z) is replaced with (z) F (z)and there is an additional source term on the right of Eq. (10) of the form $B_{\rm B} \sim 2 Q_z^2$ (z)=Q. This equation encodes two boundary conditions: $e_z j_0^{0+}$ $\hat{\mathbf{x}} \hat{\mathbf{Q}}_{z}^{3} \mathbf{j}_{0}^{0+} = \mathbf{b}_{B} = \mathbf{Q},$ and $\mathbb{Q}_z \quad \mathbf{j}_0^{0+} = \mathbf{k}_B = \mathbb{Q}$. In terms of the original , the boundary conditions are $e_z \frac{\rho_+}{R_0} = 0$, and $^{2} @_{7}^{3} = ^{0+}$ $_{\rm B}$ =Q. Charge neutrality, dz ² exp[(z) (z)] = $'_{\rm B} = Q$, is ensured for any solution to Eq. (10).

A nalytical approximations to Eq. (10) can be found in the W C and SC limits. In the W C limit, I assume the solution will decay with characteristic length . Thus, the fourth order derivative is negligible. Since (r) 1,

has the ${\tt P}\,{\tt B}\,$ equation form , given by

$$(z > 0) = 2 \ln 1 + z = \frac{p}{2}$$
: (11)

The boundary conditions are satisfied by choosing $(z < 0) = 2('=)A(e^{z='} 1)$, where ${}^{2}A^{3} = {}^{2} A = 1$. This requires $=2 = A \cdot As ! 0$, (z < 0) ! 0, and Eq. (11) becomes exact.

In the SC limit, the fourth order term dominates over the second order term near the surface. I make the additional assumption that 1, and solve

$${}^{2} \Theta_{z}^{4} = {}^{2} e^{(z)} {}^{2} e^{(0) z};$$
 (12)

which has the solution

$$(z > 0) = {}^{2}e^{(0)} e^{z} = 1 :$$
 (13)

Applying the boundary conditions, $(z < 0) = (2 = x^2) = (1 - 2 = x^2) \exp(z = x)$ 1] and $(z = x^2) = (1 - 2 = x^2) = (1 - 2 = x^2)$

 $^{2}=^{2})\exp[$ (0)]. The exponential SC density is recovered for large . This solution also becomes exact as ! 1.

For z ', (z) 1 and Eq. (10) has an approximate solution given by Eq. (11). The fourth order derivative

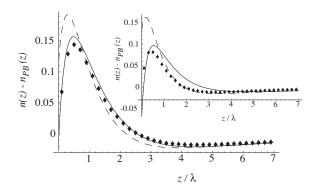


FIG.1: Normalized density di erence, $n(z) = n_{PB}(z)$, as a function of z = for = 100 (= 10 in inset). Solutions to Eq. (10) (solid line) are compared to num erical simulations from Ref. [14] (diam onds) and the TCT from Ref. [16] (dashed line).

can be neglected in this limit because is exponentially suppressed by (0) being large. Therefore, the density at large distances is PB-like and is controlled by a renorm alized G ouy-Chapman length, ren = $\overline{2}$ = exp[(0)]. This is in agreement with the arguments of Burak et al. [16], which also exhibits a crossover to a slow decay far from the surface. Using (z), I obtain the estimate ln (ren =) = [1 e^{\frac{1}{16} - (2^{\circ})}].

Eq. (10) has been solved numerically for = 100and = 10 (inset). Fig. 1 plots $n(z) = n_{PB}(z)$, where $n(z) = (z)_{B}^{2} = 2$ and $n_{PB}(z) = 1 = (1 + z =)^{2}$ is the norm alized Poisson-Boltzm ann density. These num erical solutions are compared to actual simulation data from Ref. [14] (courtesy of A. Moreira) and show quite good agreem ent. Furtherm ore, Eq. (10) outperform s the TCT (shown as dashed lines using data provided by Y.Burak from Ref. [16]). The nonperturbative function (z) is an important component of this num erical agreem ent; when a virial expansion in $_0$ is used to compute $\ln Z_s$ (equivalent to setting (z) = F(z) at low est order), the agreem ent with the sim ulation data is only slightly better than the TCT and not nearly as good as Fig. 1. A more careful evaluation of (z) is likely to improve these results further. To be clear, the value for r_0 used in Fig. 1 is simply an estim ate of the real correlation hole size, which may dier up to a factor of order one depending on the m odel used. Though there is still very good agreem ent for other reasonable values of r_0 , $r_0 = 1$ $'_{\rm B}$ =2 seems to give the best agreem ent with simulations. In contrast to the = 10 and 100 results, the density at = 1 always decays faster than the Poisson-Boltzm ann density (not shown). This is precisely where both the short and longdistance expansions in the interpolation scheme attain their maximum error, and it is possible that including higher order term s m ay im prove this.

The SC expansion can be reconstructed in this fram e-

work as an asymptotic expansion around the = 1 lim it by considering the higher order terms in $_{\rm O}$ for $\ln Z_{\rm s}$. Here we sketch this result: substituting the conjectured asymptotically exact result $\sim_0 = 2e^{z=} = (\gamma_{\rm B}^{-2})$ into h i, the rst order correction can be computed. It is straightforward to show that this gives only the nite part of the rst order SC correction as ! 1, and therefore that this correction vanishes in this lim it [12]. This occurs because the delta function in γ_0 exactly cancels the divergence from \sim_0 as ! 1. Higher order term swill also vanish in this lim it, and an asymptotic expansion can be constructed in powers of 1= which agrees exactly with SC up to rst order and which I conjecture also agrees at all orders. It is interesting that, although no explicit renorm alization is necessary in the modi ed expansion,

(z) arises to shift the fugacity 2 in a similar manner as the SC renorm alization. A more system atic accounting of these corrections is left for future work.

D espite the quantitative agreem ent, the modi ed SC expansion suggests a di erent physical picture of the strong-coupling limit: the corrections to the SC limit arise from the interactions between only those counterions that have made excursions away from the wall, as m easured by γ_0 . It is clear that the density of these excited counterions become es small for large , and that the SC limit becomes exact. The function (z) encodes the interaction of these excitations with their z = 0 correlation holes, and becomes in portant at intermediate coupling, once counterions get far enough from the surface. Interestingly, this correlation hole picture has already been described in the context of W igner crystal-like structural correlations for multivalent ions [3, 18] and in the interpretation of the TCT [16].

This scheme also provides a natural fram ework to compute the counterion free energy, which is obscured by the traditional SC expansion [12]. This is given by F = S (i) $N = (k_B T)$, where N is the number of counterions,

is the mean-eld long range potential, and the chemical potential is related to ² by = $k_B T \ln (^2 a^3 = k_B)$. Since ² depends exponentially on (0), nonperturbative correlations also play a role in the free energy, and subsequently in the interaction between two surfaces at separations where the SC expansion cannot be applied. This will be explored in a future publication.

To sum marize, I have computed the counterion density around a charged surface using a scheme to decom pose the C oulomb interaction into short and long distance components. Each is treated with di erent approximations. For large, we recover the SC results and for small we recover the W C Poisson-Boltzm ann density. At intermediate coupling, the model agrees very well with the simulation data, and depends crucially on a nonperturbative correlation correction whose form we have estimated. These correlations also play a role in determ ining the renormalized G ouy-Chapman length when the densities recovers its Poisson-Boltzm an form far from the surface.

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- [1] A.Yu.Grosberg, T.T.Nguyen, and B.J.Shklovskii, Rev. Mod.Phys. 74, 329 (2002); Y.Levin, Rep.Prog.Phys. 65, 1577 (2002); A.G. Moriera, R.R.Netz in Electrostatic E ects in Soft Matter and Biophysics, edited by C.Holm, P.Kekiche, and R.Podgornik (Kluwer Acad. Pub., Boston, 2001).
- [2] V.I.Pereland B.I.Shklovskii, Physica A 274, 446 (1999).
- [3] B.I. Shklovskii, Phys. Rev. E 60, 5802 (1999).
- [4] P.K ekiche, S.M arôelja, T J. Senden, and V E. Shubin, J. Chem. Phys. 99, 6098 (1993).
- [5] B.-Y. Ha and A.J. Liu, Phys. Rev. Lett. 79, 1289 (1997)
- [6] V A . B loom eld, B iopolymers 31, 1471 (1991)
- [7] R. Podgomik, D. Rau, and V A. Parsegian, Biophys. J. 66, 962 (1994)
- [8] A E. Larson and D G. G rier, Nature (London) 385, 230 (1997)
- [9] A W C. Lau and P. Pincus, Phys. Rev. E 66, 041501 (2002)
- [10] A W C.Lau, D.Levine, and P.Pincus, Phys. Rev. Lett. 84, 4116 (2000)
- [11] R.R.Netz and H.Orland, Eur.Phys.J.E 1, 203 (2000).
- [12] R.R.Netz, Eur.Phys.J.E 5, 557 (2001).
- [13] A G. M oreira and R R. Netz, Phys. Rev. Lett. 87, 078301 (2001).
- [14] A.G. Moreira and R.R. Netz, Eur. Phys. J. E 8, 33 (2002).
- [15] JD.W eeks, D.Chandler, H & Andersen, J.Chem. Phys. 54, 5237 (1971); D.Chandler, JD.W eeks, H & Andersen, Science 220, 787 (1983).
- [16] Y.Burak, D.Andelman, and H.Orland, Phys. Rev. E, 70, 016102 (2004).
- [17] For a simple and elegant proof, see reference [11].
- [18] T.T. Nguyen, A. Yu. Grosberg, B.I. Shklovskii, Phys. Rev.Lett. 85, 1568 (2000); T.T. Nguyen, A.Yu. Grosberg, B.I. Shklovskii, J. Chem. Phys. 113, 3 (2000).